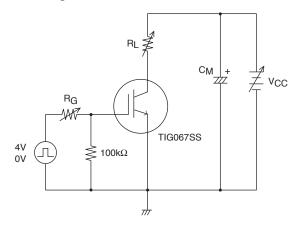
TIG067SS

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
Farameter	Symbol	Conditions	min	typ	max	Offic
Collector-to-Emitter Breakdown Voltage	V(BR)CES	I _C =2mA, V _{GE} =0V	400			V
Collector-to-Emitter Cutoff Current	ICES	V _{CE} =320V, V _{GE} =0V			10	μΑ
Gate-to-Emitter Leakage Current	IGES	V _{GE} =±6V, V _{CE} =0V			±10	μA
Gate-to-Emitter Threshold Voltage	V _{GE} (off)	V _{CE} =10V, I _C =1mA	0.4		1.0	V
Collector-to-Emitter Saturation Voltage	V _{CE} (sat)	I _C =150A, V _{GE} =4V		3.8	5	V
Input Capacitance	Cies			5100		pF
Output Capacitance	Coes	V _{CE} =10V, f=1MHz		59		pF
Reverse Transfer Capacitance	Cres			43		pF
Fall Time	t _f	I_C =150A, V_{CC} =320V, Resistor load V_{GE} =4V, R_G =36 Ω		270		ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Fig1 Large Current R Load Switching Circuit

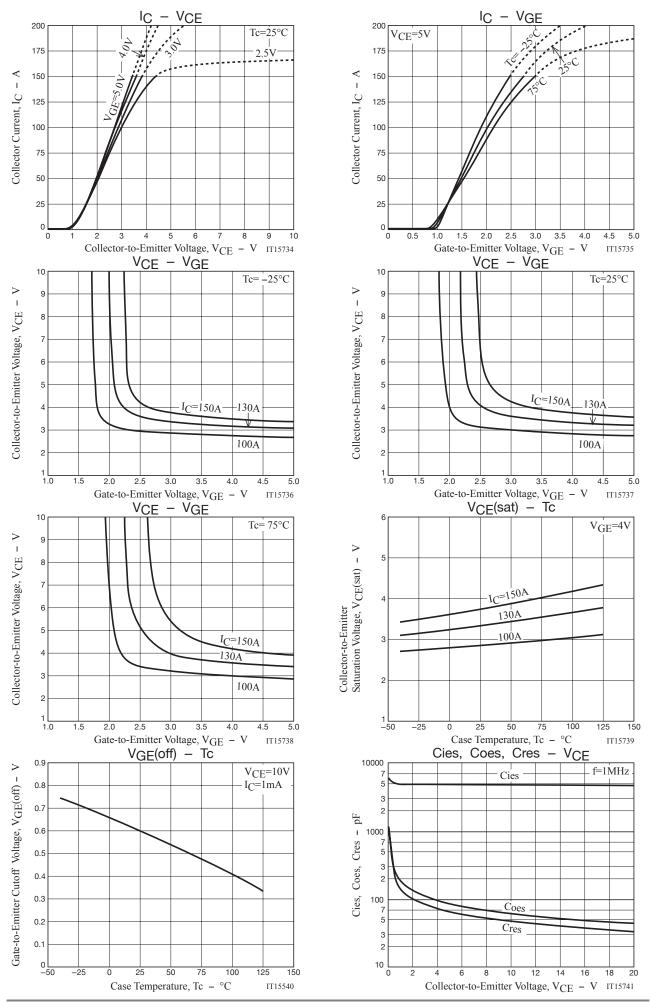


Note1. Gate Series Resistance $R_G \ge 36\Omega$ is recommended for protection purpose at the time of turn OFF. However, if $dv / dt \le 1500$ / μs is satisfied at customer's actual set evaluation, $R_G < 36\Omega$ can also be used.

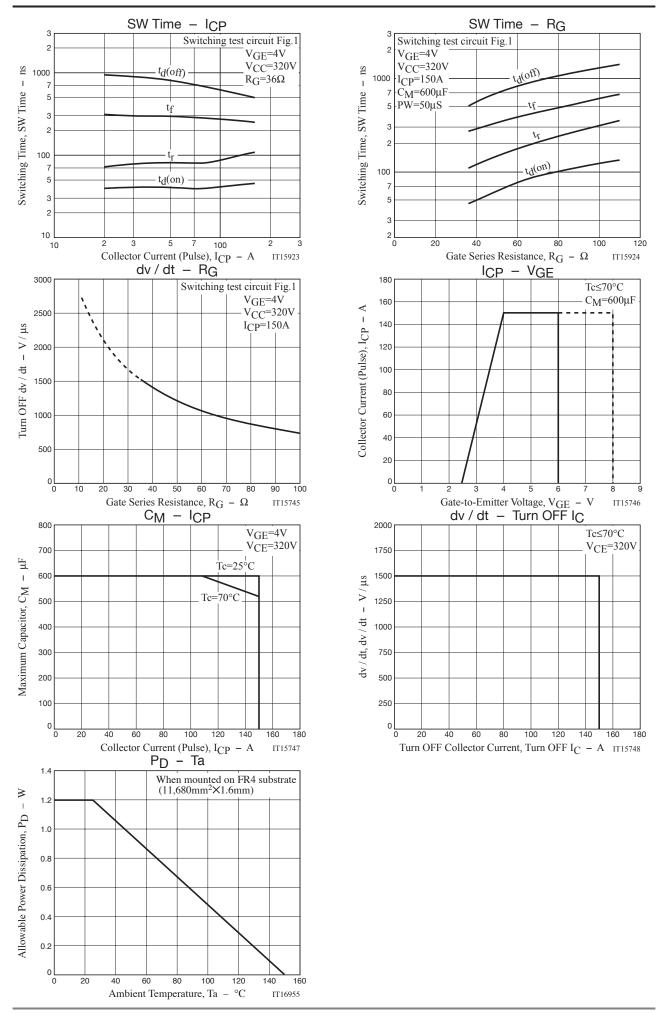
Note2. The collector voltage gradient dv / dt must be smaller than 1500V / µs to protect the device when it is turned off.

ORDERING INFORMATION

Device	Package	Shipping	memo		
TIG067SS-TL-2W	SOIC8	2,500pcs./reel	Pb-Free and Halogen Free		



TIG067SS

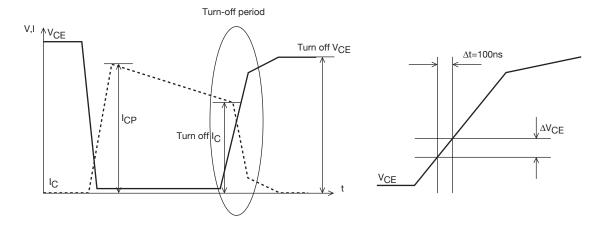


Definition of dv/dt

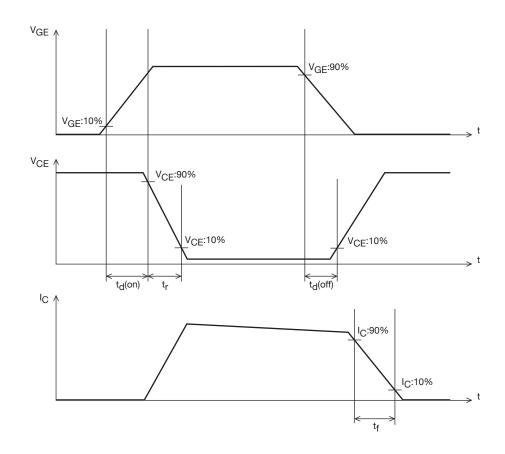
dv/dt is defined as the maximum slope of the below VCE curve during turn-off period. dv/dt= Δ VCE/ Δ t= Δ VCE/100ns

Overall waveform

Enlarged picture of turn-off period



Definition of Switching Time

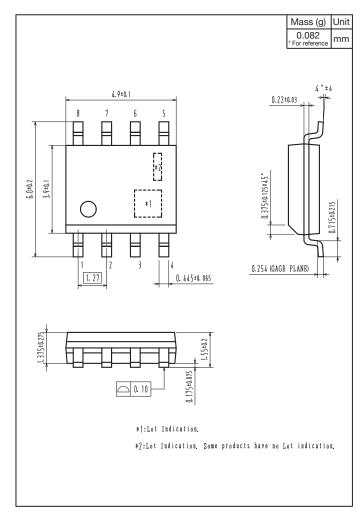


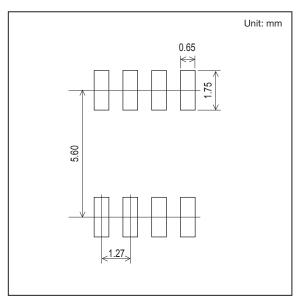
TIG067SS

Outline Drawing

TIG067SS-TL-2W

Land Pattern Example





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